

# P-CHANNEL MOS FIELD EFFECT POWER TRANSISTOR 2SJ328, 2SJ328-Z

## SWITCHING P-CHANNEL POWER MOS FET INDUSTRIAL USE

### DESCRIPTION

The 2SJ328 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

### FEATURES

- Low On-state Resistance  
 $R_{DS(on)} = 48 \text{ m}\Omega$  TYP. ( $V_{GS} = -10 \text{ V}$ ,  $I_D = -10 \text{ A}$ )  
 $R_{DS(on)} = 85 \text{ m}\Omega$  TYP. ( $V_{GS} = -4 \text{ V}$ ,  $I_D = -8 \text{ A}$ )
- Low  $C_{iss}$   $C_{iss} = 2150 \text{ pF}$  TYP.
- Built-in G-S Gate Protection Diodes

### QUALITY GRADE

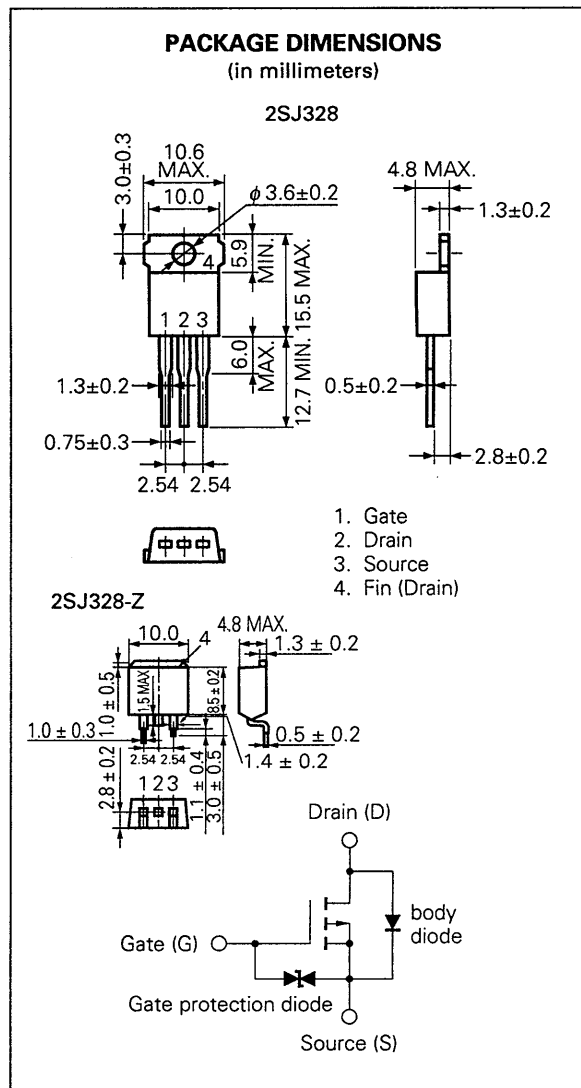
Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

### ABSOLUTE MAXIMUM RATINGS ( $T_a = 25 \text{ }^\circ\text{C}$ )

Drain to Source Voltage	$V_{DSS}$	-60	V
Gate to Source Voltage	$V_{GSS(AC)}$	$\mp 20$	V
Gate to Source Voltage	$V_{GSS(DC)}$	-20, +10	V
Drain Current (DC)	$I_{D(DC)}$	$\mp 20$	A
Drain Current (pulse)	$I_{D(pulse)^*}$	$\mp 80$	A
Total Power Dissipation ( $T_c = 25 \text{ }^\circ\text{C}$ )	$P_{T1}$	75	W
Total Power Dissipation ( $T_a = 25 \text{ }^\circ\text{C}$ )	$P_{T2}$	1.5	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$ MAX.
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

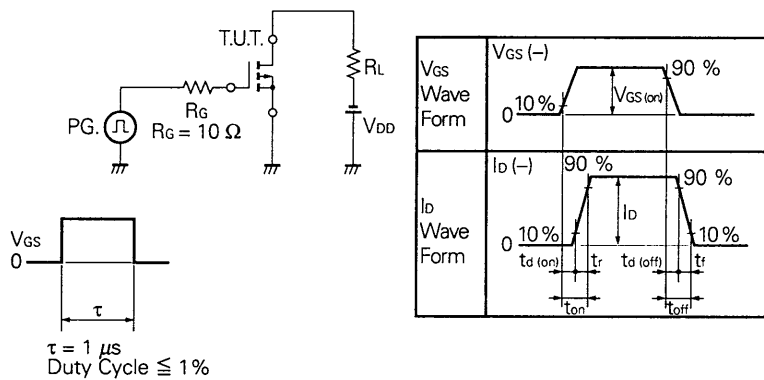
\*  $PW \leq 10 \mu\text{s}$ , Duty Cycle  $\leq 1 \%$



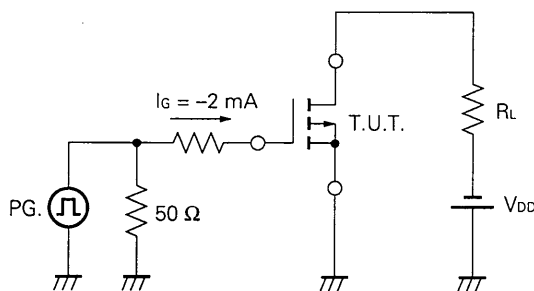
**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-state Resistance	R <sub>DS(on)</sub>		48	60	mΩ	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -10 A
Drain to Source On-state Resistance	R <sub>DS(on)</sub>		85	110	mΩ	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -8 A
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub>	-1.0	-1.5	-2.0	V	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA
Forward Transfer Admittance	y <sub>fs</sub>	8.0	13		S	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -10 A
Drain Leakage Current	I <sub>DSS</sub>			-10	μA	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0
Gate to Source Leakage Current	I <sub>GSS</sub>			±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Input Capacitance	C <sub>iss</sub>		2 150		pF	V <sub>DS</sub> = -10 V V <sub>GS</sub> = 0 f = 1 MHz
Output Capacitance	C <sub>oss</sub>		1 100		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		530		pF	
Turn-On Delay Time	t <sub>d(on)</sub>		40		ns	V <sub>GS(on)</sub> = -10 V V <sub>DD</sub> = -30 V I <sub>D</sub> = -10 A, R <sub>G</sub> = 10 Ω R <sub>L</sub> = 3.0 Ω
Rise Time	t <sub>r</sub>		180		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>		240		ns	
Fall Time	t <sub>f</sub>		230		ns	
Total Gate Charge	Q <sub>G</sub>		85		nC	V <sub>GS</sub> = -10 V I <sub>D</sub> = -20 A V <sub>DD</sub> = -48 V
Gate to Source Charge	Q <sub>GS</sub>		7		nC	
Gate to Drain Charge	Q <sub>GD</sub>		35		nC	
Diode Forward Voltage	V <sub>SD</sub>		1.0		V	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0
Reverse Recovery Time	t <sub>rr</sub>		120		ns	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0
Reverse Recovery Charge	Q <sub>rr</sub>		260		nC	di/dt = 50 A/μs

**Test Circuit 1: Switching Time**

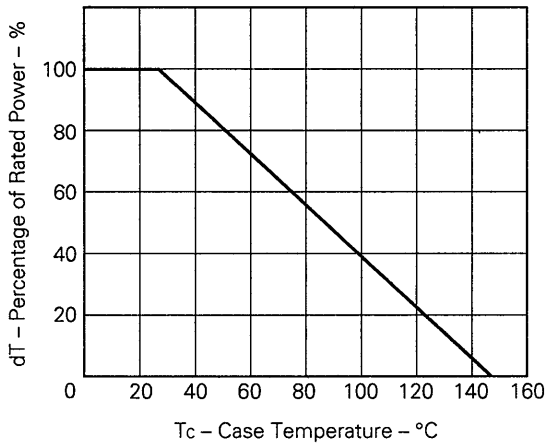


**Test Circuit 2: Gate Charge**

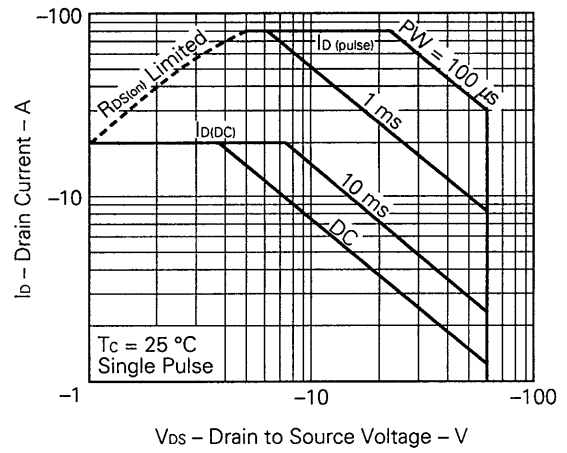


ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)

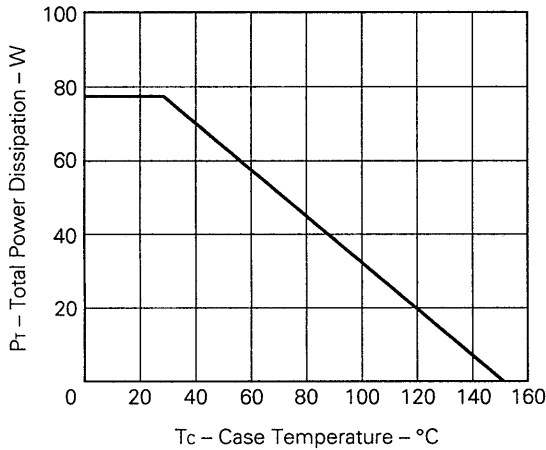
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



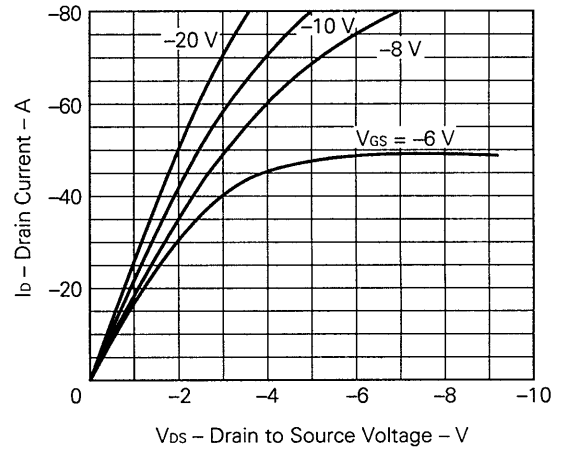
FORWARD BIAS SAFE OPERATING AREA



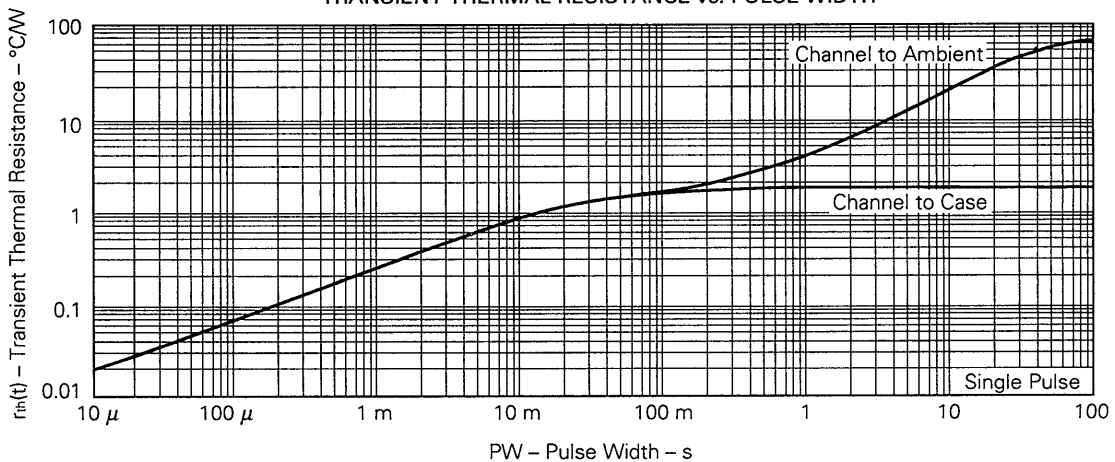
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



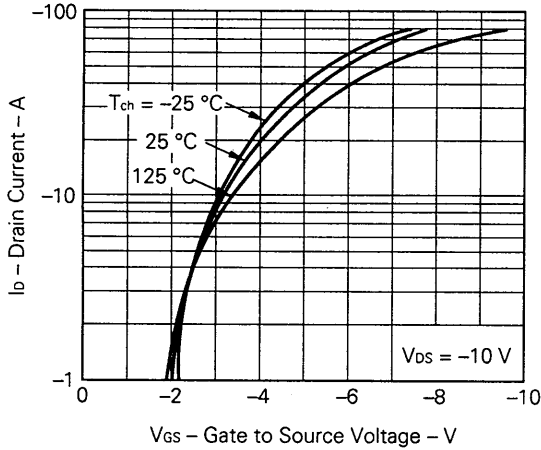
DRAIN CURRENT vs. DRAIN TO SOURCE CURRENT



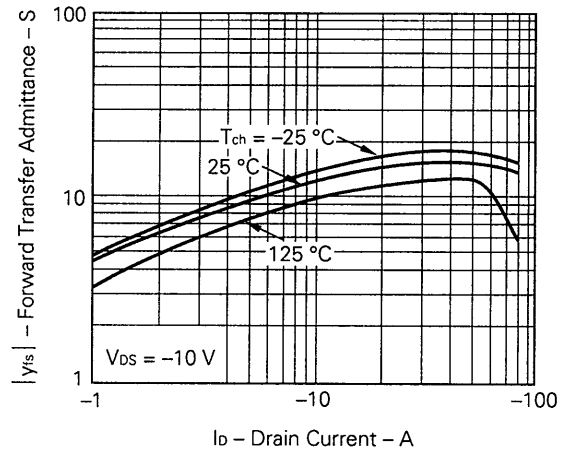
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



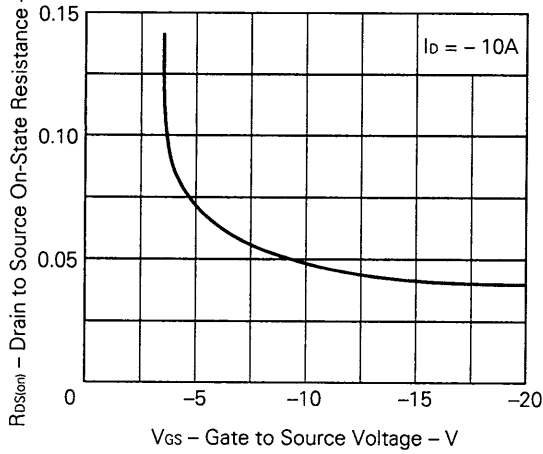
TRANSFER CHARACTERISTICS



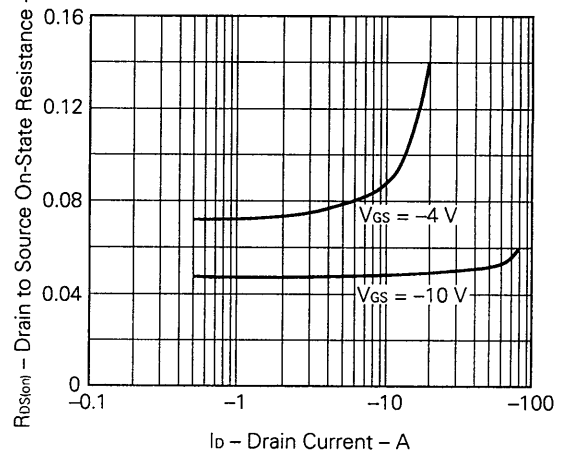
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



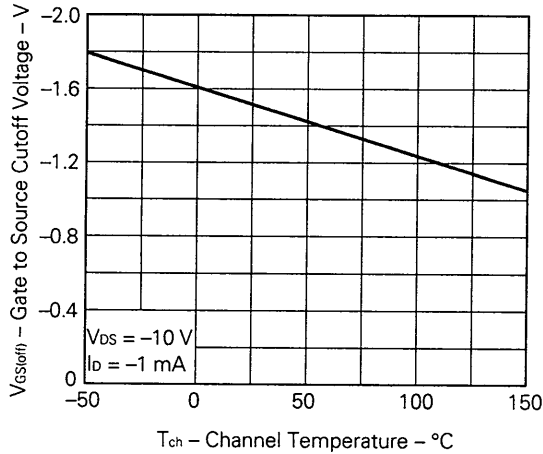
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



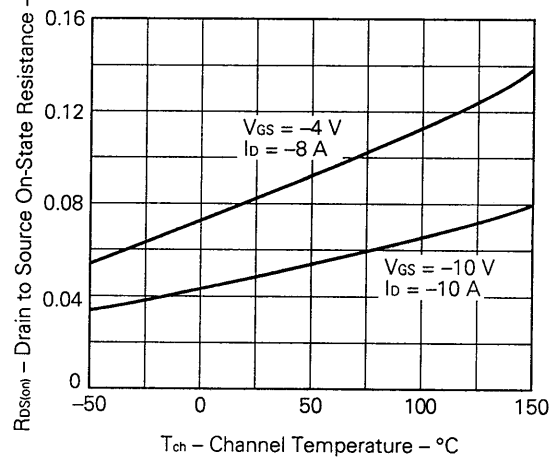
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



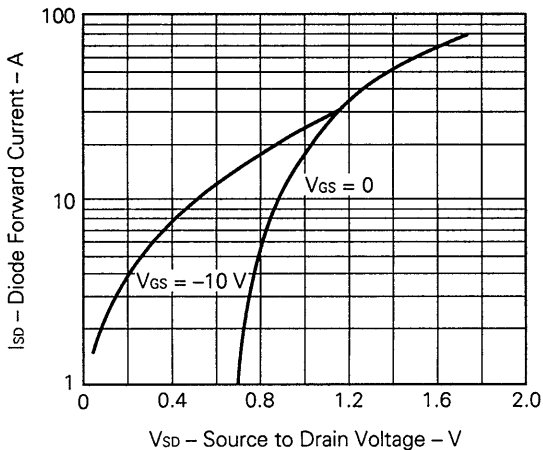
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



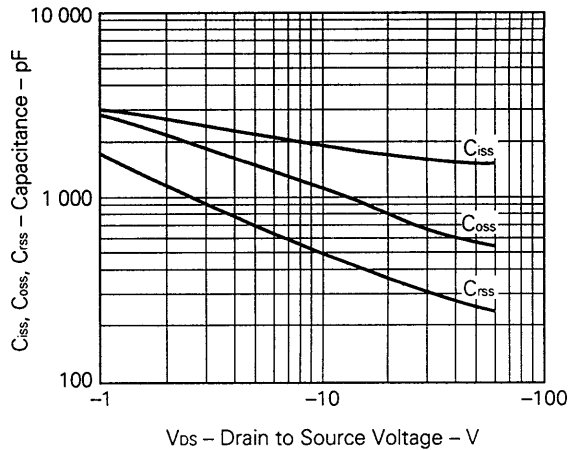
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



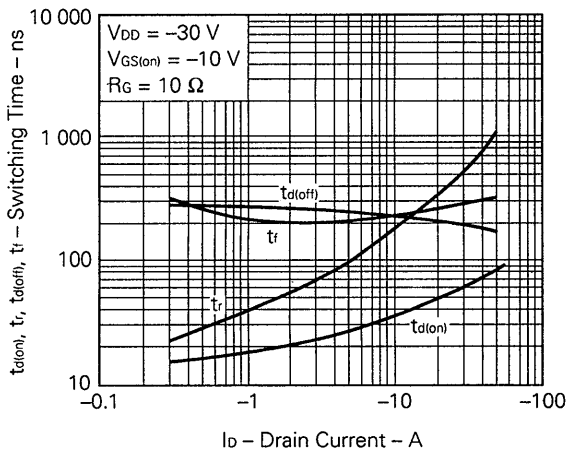
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



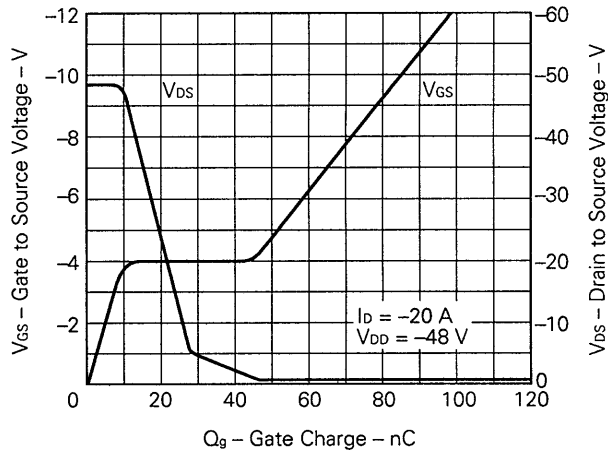
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



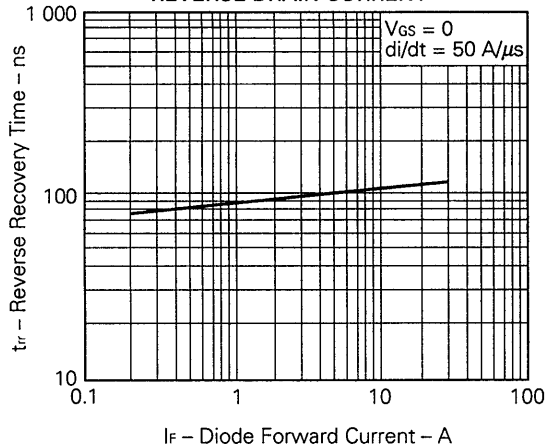
SWITCHING CHARACTERISTICS



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



REVERSE RECOVERY TIME vs. REVERSE DRAIN CURRENT



**Reference**

Application note name	No.
Safe operating area of Power MOS FET.	TEA-1034
Application circuit using Power MOS FET.	TEA-1035
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207

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